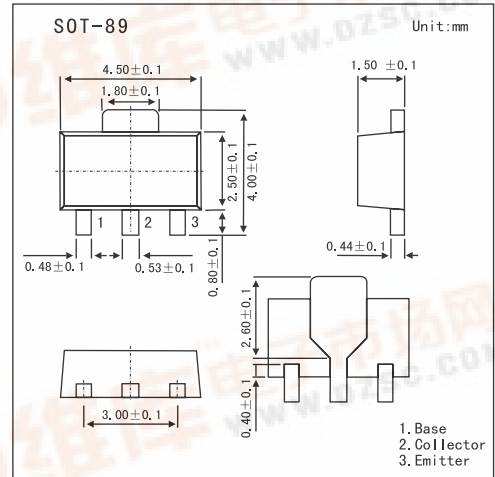


SMD Type Transistors

Low Frequency Transistor
2SB1386

Features

- Low VCE(sat).
VCE(sat) = -0.35V (Typ.)
(IC/IB = -4A / -0.1A)
- Excellent DC current gain
- Epitaxial planar type
- PNP silicon transistor



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-30	V
Collector-emitter voltage	V _{CEO}	-20	V
Emitter-base voltage	V _{EBO}	-6	V
Collector current	I _C	-5	A
Collector current(Pulse)	I _{CP} *	-10	A
Collector power dissipation	P _C	0.5	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Single pulse, Pw=10ms

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CB0}	I _C =-50μA	-30			V
Collector-emitter breakdown voltage	BV _{CEO}	I _C =-1mA	-20			V
Emitter-base breakdown voltage	BV _{EBO}	I _E =-50μA	-6			V
Collector cutoff current	I _{CBO}	V _{CB} =-20V			-0.5	μA
Emitter cutoff current	I _{EBO}	V _{EB} =-5V			-0.5	μA
DC current transfer ratio	V _{CE(sat)}	I _C =-4A, I _B =-0.1A			-1	V
Collector-emitter saturation voltage	h _{FE}	V _{CE} =-2V, I _C =-0.5A	82		390	
Transition frequency	C _{ob}	V _{CE} =-6V, I _E =50mA, f=30MHz		120		MHz
Output capacitance	f _r	V _{CB} =-20V, I _E =0A, f=1MHz		60		pF

hFE Classification

Marking	BH		
	P	Q	R
hFE	82~180	120~270	180~390

